

1. Scope

The present specifications shall apply to an SJPE-H4.

2. Outline

Type	Silicon Schottky Barrier Diode
Structure	Resin Molded
Applications	High Frequency Rectification

3. Flammability

UL94V-0(Equivalent)

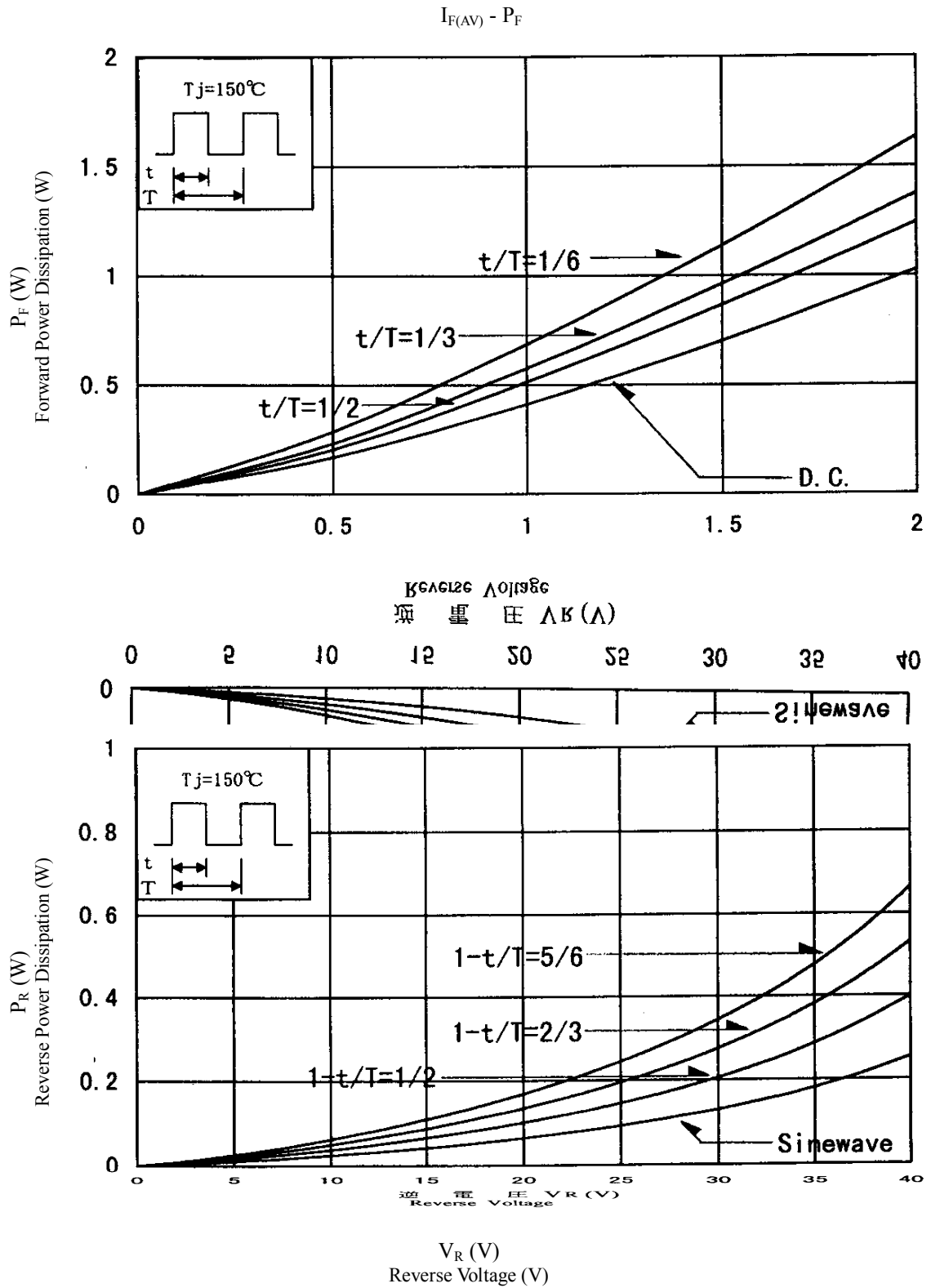
4. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	40	—
2	Peak Reverse Voltage	V_{RM}	V	40	—
3	Average Forward Current	$I_{F(AV)}$	A	2.0	Refer to Derating of 7
4	Peak Surge Forward Current	I_{FSM}	A	40	Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	8.0	$1\text{msec} \leq t \leq 10\text{msec}$
6	Junction Temperature	T_j	$^{\circ}C$	-40~+150	—
7	Storage Temperature	T_{stg}	$^{\circ}C$	-40~+150	—

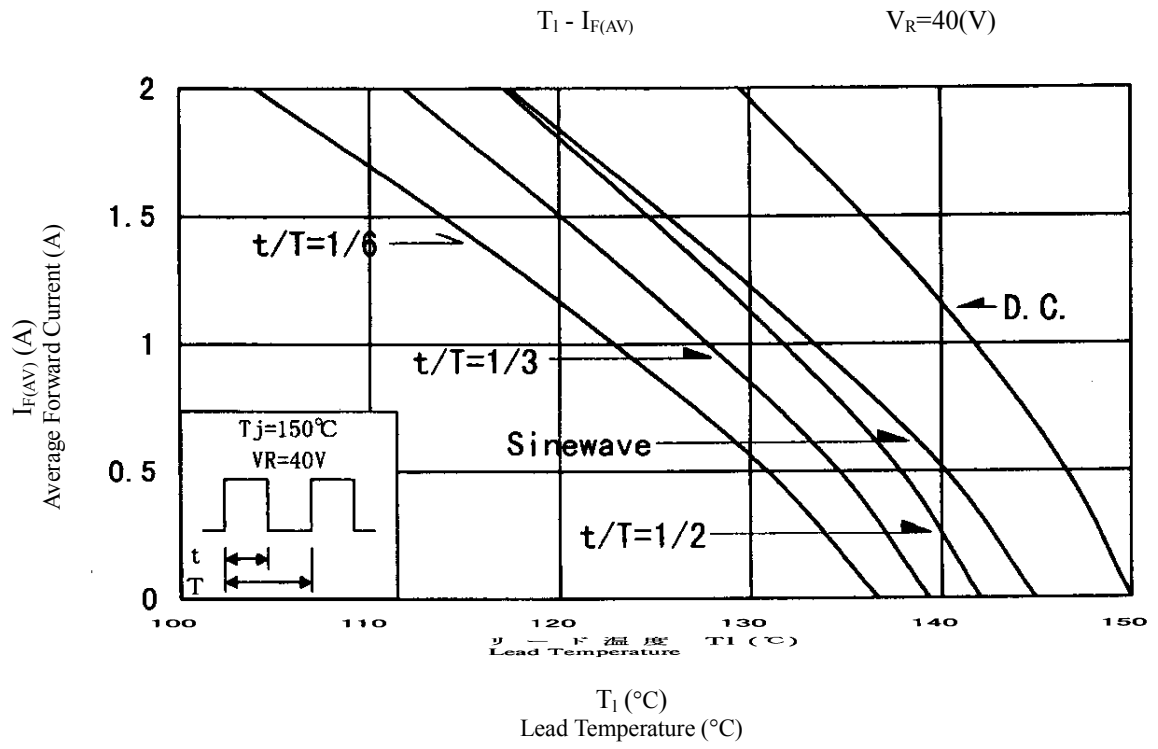
5. Electrical characteristics ($T_a=25^{\circ}C$, unless otherwise specified)

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	0.6 max.	$I_F=2.0A$
2	Reverse Leakage Current	I_R	μA	50 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	20 max.	$V_R=V_{RM}, T_j=150^{\circ}C$
4	Thermal Resistance	$R_{th(j-l)}$	$^{\circ}C/W$	20 max.	Between Junction and lead

6. Characteristics

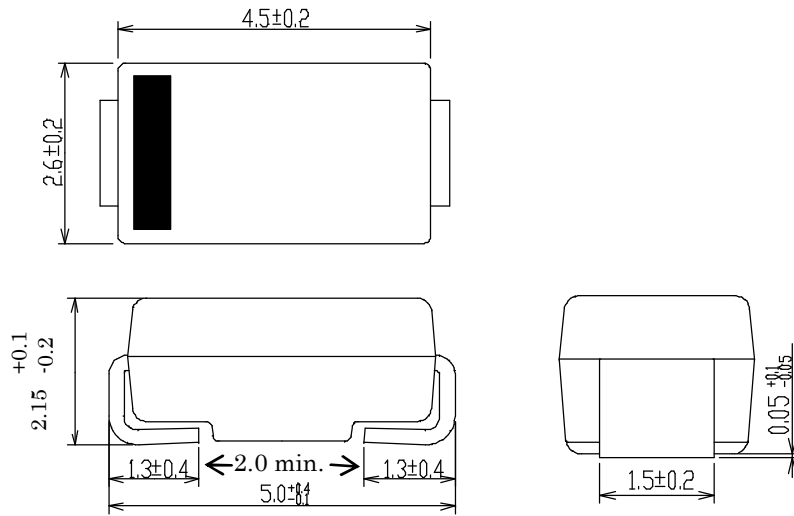


7. Derating



8. Package information

8-1 Package type, physical dimensions and material

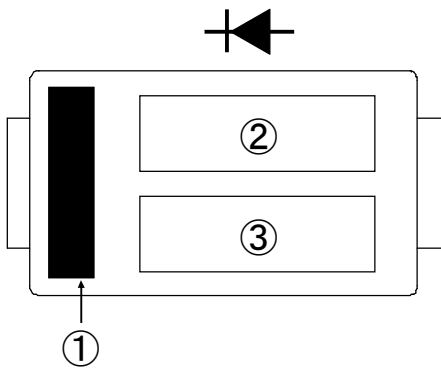


単位 : mm
Dimensions in mm

8-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3 Marking



Polarity marking (Cathode band)

Type number
SJPE-H4 as abbreviated of EH4

Lot number
Example) 6718
6: Last number of Year
7: Month from 1 to 9 for Jan. to Sep.
O for Oct. , N for Nov. , D for Dec.
18: Day